2SD1750, 2SD1750A

Silicon NPN triple diffusion planar type darlington

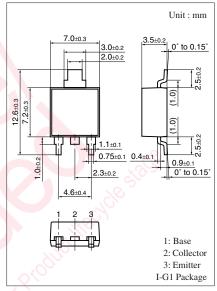
For midium speed power switching Complementary to 2SB1180 and 2SB1180A

■ Features

- High forward current transfer ratio h_{FE}
- High-speed switching
- I type package enabling direct soldering of the radiating fin to the printed circuit board, etc. of small electronic equipment

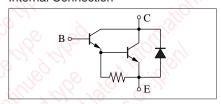
■ Absolute Maximum Ratings $T_C = 25$ °C

Parameter	Symbol	Rating	Unit	
Collector-base voltage	2SD1750	V _{CBO}	60	V
(Emitter open)	2SD1750A		80	
Collector-emitter voltage	2SD1750	V_{CEO}	60	V
(Base open)	2SD1750A		80	
Emitter-base voltage (Coll	V_{EBO}	7	V	
Collector current	I_{C}	8	A	
Peak collector current	I _{CP}	12	A	
Collector power dissipation	P _C	15	W	
	$T_a = 25^{\circ}C$		1.3	11011
Junction temperature	T_{j}	150	°C	
Storage temperature	T_{stg}	-55 to +150	°C	



Note) Self-supported type package is also prepared.

Internal Connection



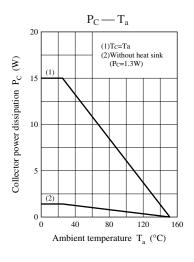
■ Electrical Characteristics $T_C = 25^{\circ}C \pm 3^{\circ}C$

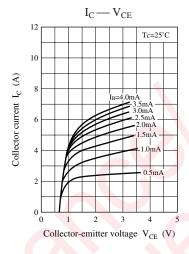
Parameter		Symbol	Conditions	Min	Тур	Max	Unit
Collector-emitter voltage	2SD1750	V _{CEO}	$I_C = 30 \text{ mA}, I_B = 0$	60)·		V
(Base open)	2SD1750A	3	The sign of	80			
Collector-base cutoff	2SD1750	I_{CBO}	$V_{CB} = 60 \text{ V}, I_{E} = 0$			100	μΑ
current (Emitter open)	2SD1750A		$V_{CB} = 80 \text{ V}, I_{E} = 0$			100	
Emitter-base cutoff current (Col	lector open)	I_{EBO}	$V_{EB} = 7 \text{ V}, I_{C} = 0$			2	mA
Forward current transfer rat	io	h _{FE1} *	$V_{CE} = 3 \text{ V}, I_{C} = 4 \text{ A}$	2 000		10 000	_
		h _{FE2}	$V_{CE} = 3 \text{ V}, I_{C} = 8 \text{ A}$	500			
Collector-emitter saturation	voltage	V _{CE(sat)}	$I_C = 4 \text{ A}, I_B = 8 \text{ mA}$			1.5	V
Base-emitter saturation volt	age	V _{BE(sat)}	$I_C = 4 \text{ A}, I_B = 8 \text{ mA}$			2.0	V
Forward current transfer rat	io	f_T	$V_{CE} = 10 \text{ V}, I_{C} = 0.5 \text{ A}, f = 1 \text{ MHz}$		20		MHz
Turn-on time		t _{on}	$I_C = 4 \text{ A}, I_{B1} = 8 \text{ mA}, I_{B2} = -8 \text{ mA}$		0.5		μs
Storage time		t _{stg}	$V_{CC} = -50 \text{ V}$		4.0		μs
Fall time		t _f			1.0		μs

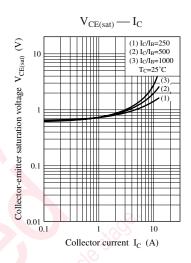
Note) 1. Measuring methods are based on JAPANESE INDUSTRIAL STANDARD JIS C 7030 measuring methods for transistors.

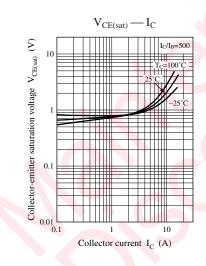
2. *: Rank classification

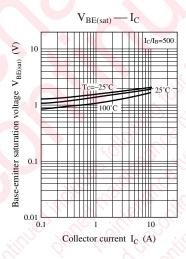
Rank	Q	Р		
$h_{\rm FE1}$	2000 to 5000	4000 to 10000		

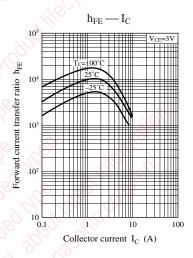


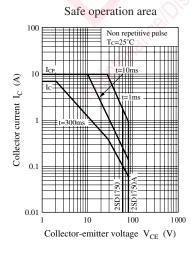


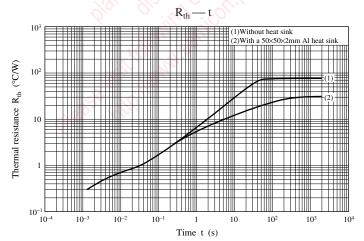












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